

Customer No.: 31561
Application No.: 10/605,214
Docket No.: 9789-US-PA

REMARKS

Present Status of the Application

This is a full and timely response to the outstanding final Office Action mailed on September 19, 2005. It is noted with great appreciation that the Examiner considers claims 5-7, 13-14 as being allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. The Office Action, however, rejected claims 1-2 and 8-9 under 35 U.S.C. § 102(b) as being anticipated by Lee et al. (US 2002/0074548) and Sasaki (USP 4,404,733), respectively.

After carefully considering the remarks set forth in this Office Action and the cited references, Applicants respectfully submitted that the presently pending claims 1-2, 5-9, 13-14 are already in condition for allowance. Reconsideration and withdrawal of the Examiner's rejection are requested.

Discussion of Office Action Rejections

The Office Action rejected claims 1-2 under 35 U.S.C. 102(e) as being anticipated by Lee et al. (US 2002/0074548 A1).

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The Office Action rejected claims 8-9 under 35 U.S.C. 102(b) as being anticipated by Lee et al. (USP 4,404,733).

Applicants respectfully traverse the 35 U.S.C §102(e) and the 102(b) rejections for at least the reasons that the prior art reference fails to teach either expressly or inherently each and every element of the claim in issue.

Claim 1 of the present invention teaches, among other things, "... forming a passivation layer on the substrate to cover the organic light emitting diode unit; and providing an ion beam to perform surface treatment on the passivation layer, wherein the ion beam is provided by ion implantation". The prior art reference Lee instead teaches forming a gate insulation layer 42 on the patterned active layer 41 of a TFT. A thin film transistor is not equivalent to an OLED unit, not to mention the gate insulation layer 42 is formed only on the amorphous silicon active layer 41 and not on a TFT. Accordingly, Lee at least fails to teach forming a passivation layer on the substrate to cover the organic light emitting diode unit of the instant case. Further, Lee teaches performing an ion shower doping to form a light doped region in the active layer 41 under the gate insulation layer 42. The present invention, however, teaches performing a surface treatment on the passivation layer, which the Office construed as equivalent to the gate insulation layer 42 of Lee. It is well understood to those skilled in the art that forming a doped region under a certain layer and performing a surface treatment on that certain layer are different. Not only the operation conditions are different, the effect and the mechanisms to achieve the end results are different. A surface treatment on a layer may merely result in an alteration of properties of the

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surface of the layer; whereas forming a doped region under the layer requires dopants to penetrate through the entire layer to form a doped region thereunder. Therefore, Lee also fails to teach the present invention in this regards.

Similarly with Sasaki, Sasaki teaches forming a gate oxide layer 13 on a substrate 11 and performing an ion implantation to form source/drain regions in the substrate 11. Sasaki fails to teach providing an ion beam to perform surface treatment on the passivation layer for at least the same reasons discussed above. Moreover, the present invention teaches forming a plastic layer on the passivation layer. Sasaki, on the other hand, teaches forming a PSG layer on the aluminum layer 24 and the insulating layer 17. Not only a PSG layer can not be construed as a plastic layer, the PSG layer is formed on the aluminum layer 24 and the insulating layer 17, rather than on the gate oxide layer 13, which the Office considered as equivalent to the passivation layer of the instant case. Applicants thereby respectfully submit that Sasaki also fails to render claim 8 anticipated in this regards.

For at least these reasons, Applicants respectfully assert that claims 1-2 and 8-9 patentably define over Lee and Sasaki, respectively. Since claims 5-7 and 9, 13-14 are dependent claims which further define the invention recited in claims 1 and 8, respectively, Applicant respectfully assert that these claim is also in condition for allowance. Therefore, reconsideration and withdrawal of these rejections are respectfully requested.

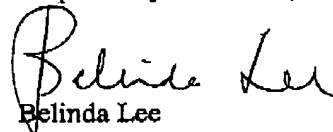
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CONCLUSION

For at least the foregoing reasons, it is believed that the presently pending claims 1-2, 5-9 and 12-14 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Respectfully submitted,


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